

Please replace the abstract of the disclosure with the following amended abstract:

#### ABSTRACT

~~When Polishing~~ a nitride semiconductor monocrystalline wafer ~~is polished,~~  
~~leaves it with~~ a process-transformed layer ~~is produced. Etching is required in order~~  
~~to remove~~ ~~[[the]]~~ The process-transformed layer has to be etched to be removed.  
~~Being that~~ The chemical inertness of nitride semiconductor materials ~~are chemically~~  
~~inert~~ has, however, precluded suitable etching ~~does not exist~~. Although potassium  
hydroxide, for example, or sulfuric acid have been proposed as GaN etchants, their  
ability to corrosively remove material from the Ga face is weak. Dry etching utilizing  
a halogen plasma is carried out in order to remove the process-transformed layer.  
The Ga face can be etched off with the halogen plasma. Nevertheless, owing to the  
dry etching, a problem arises again—surface contamination due to metal particles.  
To address the problem, wet etching with, as the etchant, solutions such as HF +  
H<sub>2</sub>O<sub>2</sub> H<sub>2</sub>O<sub>2</sub>, H<sub>2</sub>SO<sub>4</sub> H<sub>2</sub>SO<sub>4</sub> + H<sub>2</sub>O<sub>2</sub> H<sub>2</sub>O<sub>2</sub>, HCl + H<sub>2</sub>O<sub>2</sub> H<sub>2</sub>O<sub>2</sub>, or HNO<sub>3</sub> HNO<sub>3</sub>, which  
~~have no selectivity~~ are nonselective for Ga/N faces, have metal etching capability,  
and have an oxidation-reduction potential of 1.2 V or more, is performed.